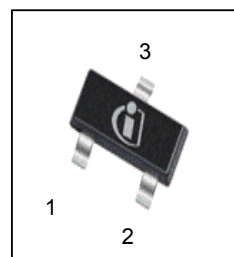
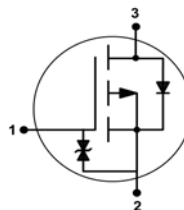


**OptiMOS™ P3 Small-Signal-Transistor**
**Features**

- P-channel
- Enhancement mode
- Logic level (4.5V rated)
- ESD protected
- Qualified according to AEC Q101
- 100% lead-free; RoHS compliant
- Halogen-free according to IEC61249-2-21


**Product Summary**

|                  |                        |      |           |
|------------------|------------------------|------|-----------|
| $V_{DS}$         |                        | -30  | V         |
| $R_{DS(on),max}$ | $V_{GS}=-10\text{ V}$  | 80   | $m\Omega$ |
|                  | $V_{GS}=-4.5\text{ V}$ | 130  |           |
| $I_D$            |                        | -2.0 | A         |

**PG-SOT-23**


| Type     | Package  | Tape and Reel Information | Marking | Lead Free | Packing |
|----------|----------|---------------------------|---------|-----------|---------|
| BSS308PE | PG-SOT23 | H6327: 3000 pcs/ reel     | YFs     | Yes       | Non dry |

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                           | Symbol            | Conditions                                                                                                         | Value          | Unit              |
|-------------------------------------|-------------------|--------------------------------------------------------------------------------------------------------------------|----------------|-------------------|
| Continuous drain current            | $I_D$             | $T_A=25\text{ °C}$                                                                                                 | -2.0           | A                 |
|                                     |                   | $T_A=70\text{ °C}$                                                                                                 | -1.6           |                   |
|                                     |                   | $T_A=25\text{ °C}$                                                                                                 | -8.0           |                   |
| Pulsed drain current                | $I_{D,pulse}$     | $T_A=25\text{ °C}$                                                                                                 | -8.0           |                   |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=-2\text{ A}$ , $R_{GS}=25\text{ }\Omega$                                                                      | -10.7          | mJ                |
| Reverse diode $dv/dt$               | $dv/dt$           | $I_D=-2\text{ A}$ ,<br>$V_{DS}=-16\text{ V}$ ,<br>$di/dt=-200\text{ A}/\mu\text{s}$ ,<br>$T_{j,max}=150\text{ °C}$ | 6              | kV/ $\mu\text{s}$ |
| Gate source voltage                 | $V_{GS}$          |                                                                                                                    | $\pm 20$       | V                 |
| Power dissipation <sup>1)</sup>     | $P_{tot}$         | $T_A=25\text{ °C}$                                                                                                 | 0.5            | W                 |
| Operating and storage temperature   | $T_j$ , $T_{stg}$ |                                                                                                                    | -55 ... 150    | °C                |
| ESD Class                           |                   | JESD22-A114 -HBM                                                                                                   | 2 (2kV to 4kV) |                   |
| Soldering Temperature               |                   |                                                                                                                    | 260 °C         | °C                |
| IEC climatic category; DIN IEC 68-1 |                   |                                                                                                                    | 55/150/56      | °C                |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Thermal characteristics

|                                        |            |                                 |   |   |     |     |
|----------------------------------------|------------|---------------------------------|---|---|-----|-----|
| Thermal resistance, junction - ambient | $R_{thJA}$ | minimal footprint <sup>1)</sup> | - | - | 250 | K/W |
|----------------------------------------|------------|---------------------------------|---|---|-----|-----|

#### Electrical characteristics, at $T_j=25\text{ °C}$ , unless otherwise specified

#### Static characteristics

|                                  |               |                                             |      |      |      |            |
|----------------------------------|---------------|---------------------------------------------|------|------|------|------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=-250\mu A$                  | -30  | -    | -    | V          |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=-11\mu A$               | -2.0 | -1.5 | -1.0 |            |
| Drain-source leakage current     | $I_{DSS}$     | $V_{DS}=-30V, V_{GS}=0V, T_j=25\text{ °C}$  | -    | -    | -1   | $\mu A$    |
|                                  |               | $V_{DS}=-30V, V_{GS}=0V, T_j=150\text{ °C}$ | -    | -    | -100 |            |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=-20V, V_{DS}=0V$                    | -    | -    | -5   | $\mu A$    |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=-4.5V, I_D=-1.7A$                   | -    | 88   | 130  | m $\Omega$ |
|                                  |               | $V_{GS}=-10V, I_D=-2A$                      | -    | 62   | 80   |            |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=-1.6A$   |      | 4.6  | -    | S          |

<sup>1)</sup> Performed on 40mm<sup>2</sup> FR4 PCB. The traces are 1mm wide, 70 $\mu$ m thick and 20mm long; they are present on both sides of the PCB.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Dynamic characteristics

|                              |              |                                                                                      |   |      |     |    |
|------------------------------|--------------|--------------------------------------------------------------------------------------|---|------|-----|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=-15\text{ V},$<br>$f=1\text{ MHz}$                        | - | 376  | 500 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                      | - | 196  | 261 |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                      | - | 12   | 18  |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=-15\text{ V},$<br>$V_{GS}=-10\text{ V},$<br>$I_D=-2\text{ A}, R_G=6\ \Omega$ | - | 5.6  | -   | ns |
| Rise time                    | $t_r$        |                                                                                      | - | 7.7  | -   |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                      | - | 15.3 | -   |    |
| Fall time                    | $t_f$        |                                                                                      | - | 2.8  | -   |    |

#### Gate Charge Characteristics

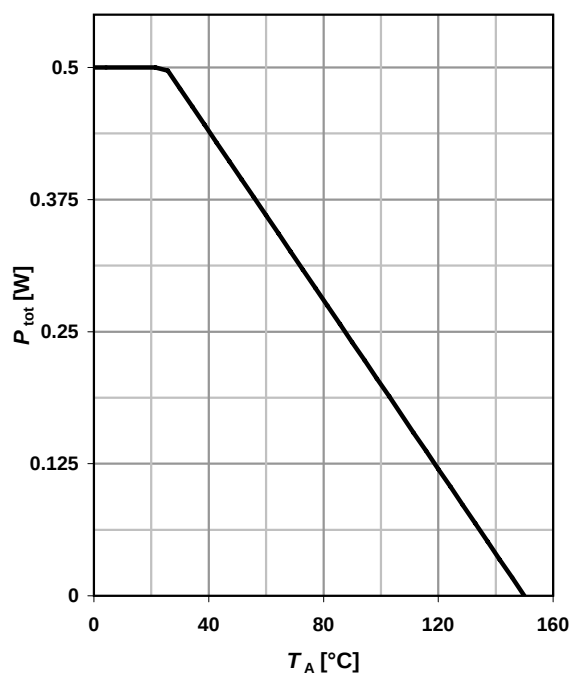
|                       |               |                                                                              |   |      |   |    |
|-----------------------|---------------|------------------------------------------------------------------------------|---|------|---|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=-15\text{ V}, I_D=-2\text{ A},$<br>$V_{GS}=0\text{ to }-10\text{ V}$ | - | -1.2 | - | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                              | - | -0.6 | - |    |
| Gate charge total     | $Q_g$         |                                                                              | - | -5.0 | - |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                              | - | -3.1 | - | V  |

#### Reverse Diode

|                                  |               |                                                                           |   |      |      |    |
|----------------------------------|---------------|---------------------------------------------------------------------------|---|------|------|----|
| Diode continuous forward current | $I_S$         | $T_A=25\text{ °C}$                                                        | - | -    | -0.4 | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                           | - | -    | -8.4 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=-2\text{ A},$<br>$T_j=25\text{ °C}$               | - | -0.8 | -1.1 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=10\text{ V}, I_F=-2\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 14   | -    | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                           | - | -5.9 | -    | nC |

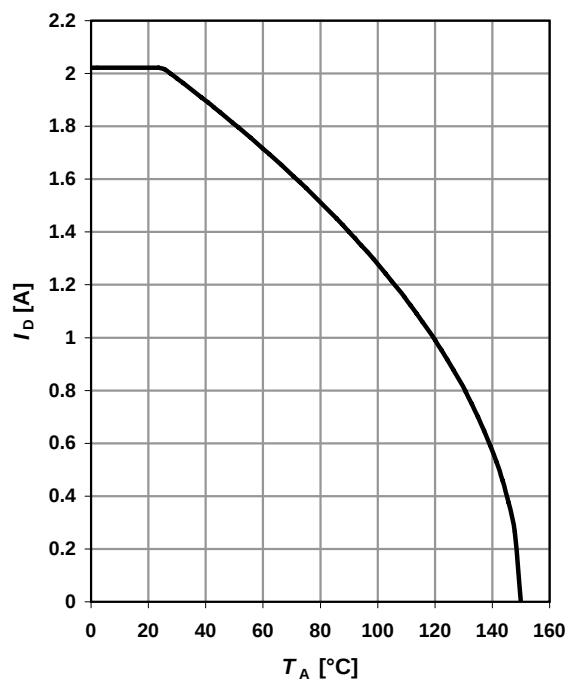
### 1 Power dissipation

$$P_{\text{tot}} = f(T_A)$$



### 2 Drain current

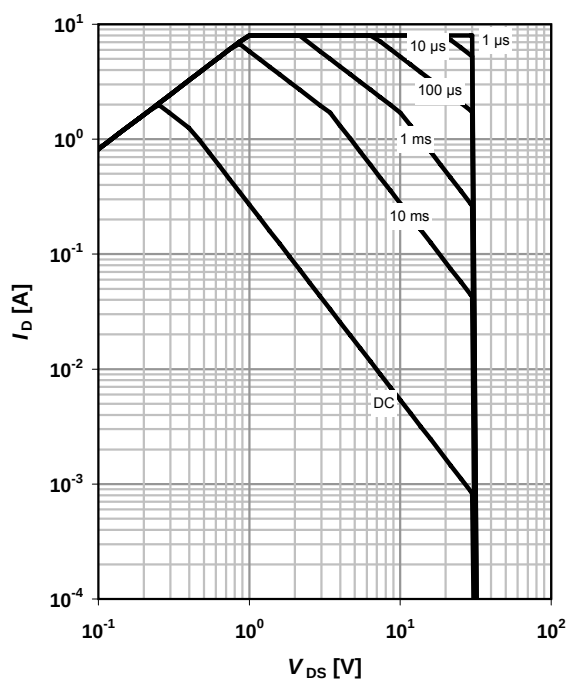
$$I_D = f(T_A); V_{\text{GS}} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_A = 25^\circ\text{C}; D = 0$$

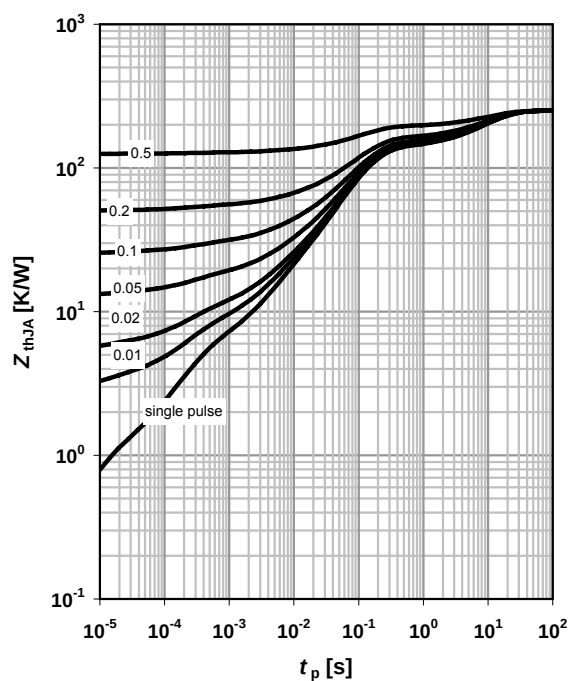
parameter:  $t_p$



### 4 Max. transient thermal impedance

$$Z_{\text{thJA}} = f(t_p)$$

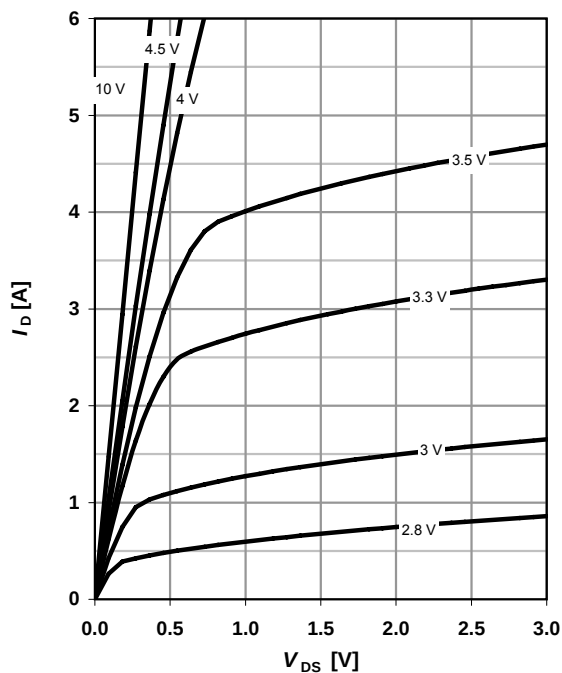
parameter:  $D = t_p/T$



### 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

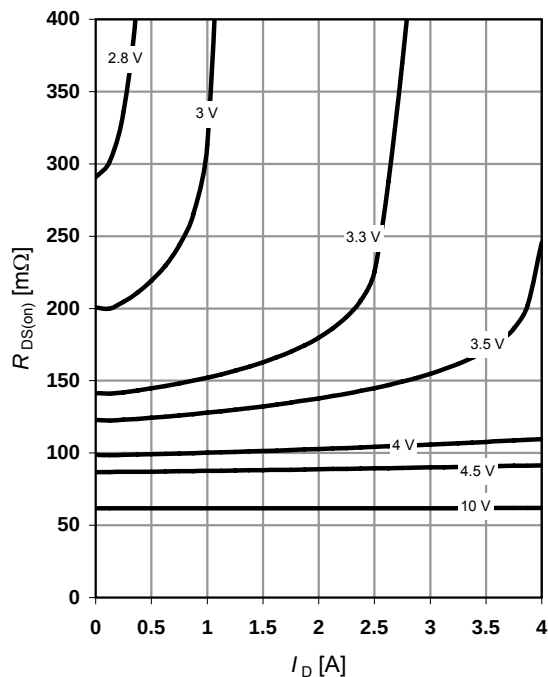
parameter:  $V_{GS}$



### 6 Typ. drain-source on resistance

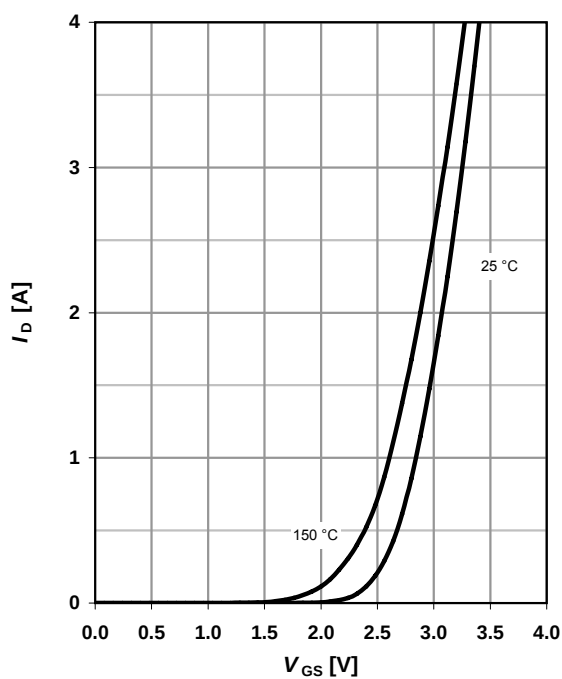
$$R_{DS(on)} = f(I_D); T_J = 25^\circ\text{C}$$

parameter:  $V_{GS}$



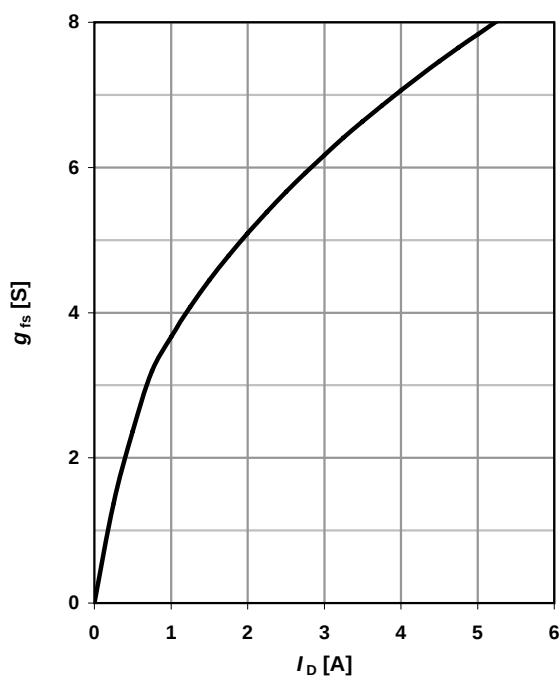
### 7 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$



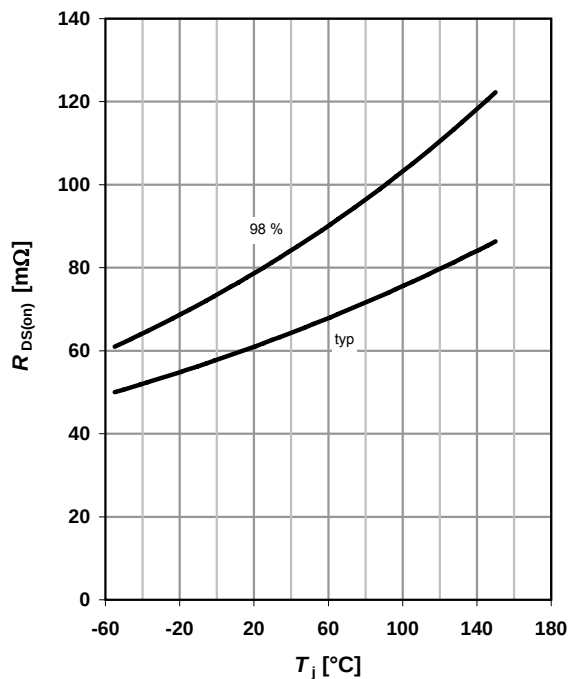
### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$



### 9 Drain-source on-state resistance

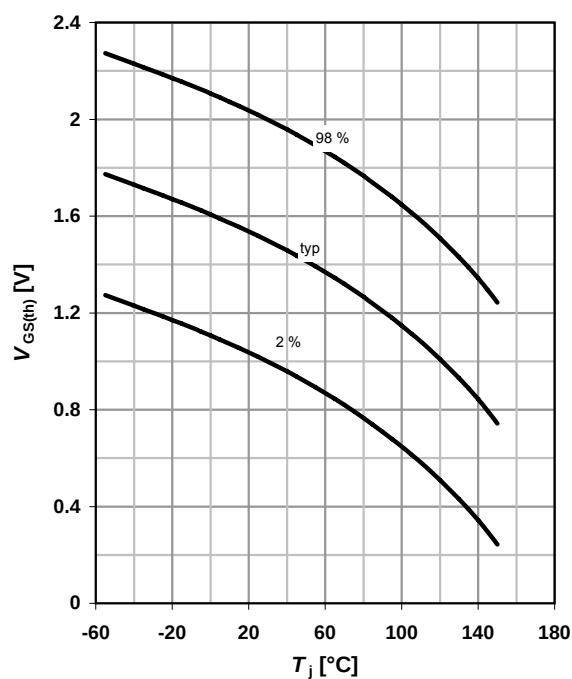
$$R_{DS(on)} = f(T_j); I_D = -2 \text{ A}; V_{GS} = -10 \text{ V}$$



### 10 Typ. gate threshold voltage

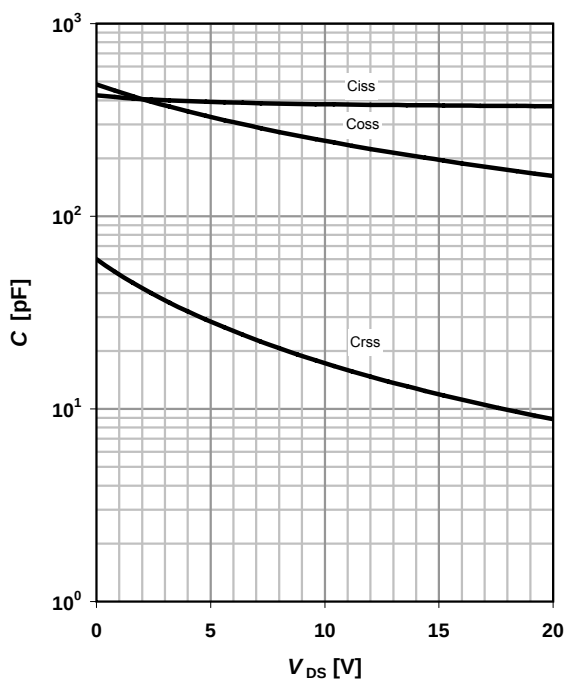
$$V_{GS(th)} = f(T_j); V_{DS} = V_{GS}; I_D = 11 \mu\text{A}$$

parameter:  $I_D$



### 11 Typ. capacitances

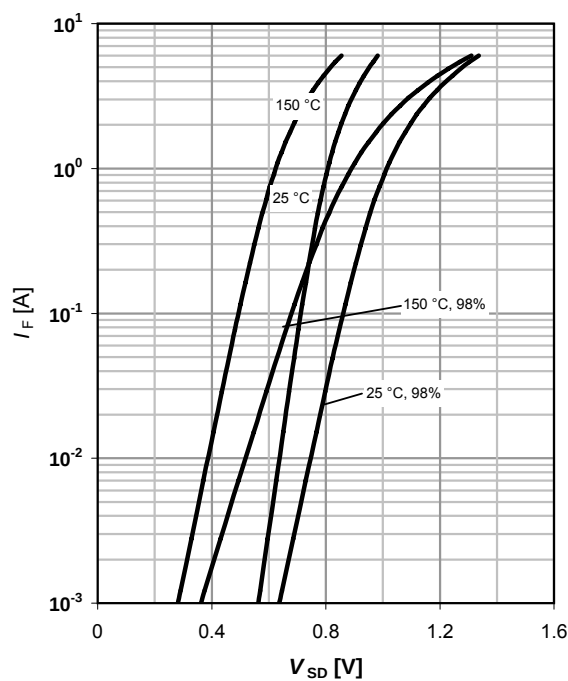
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25^\circ\text{C}$$



### 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

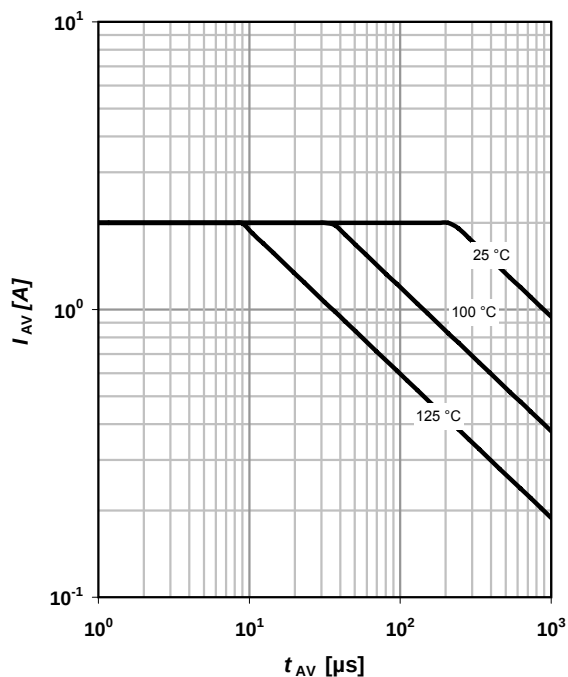
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

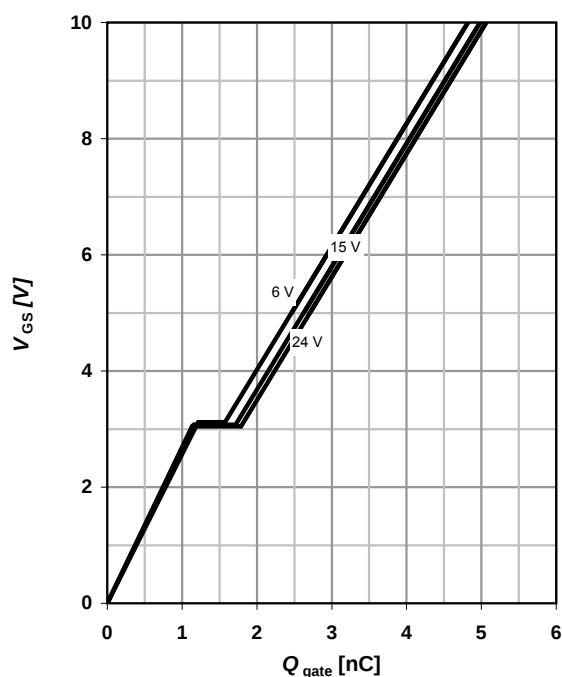
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

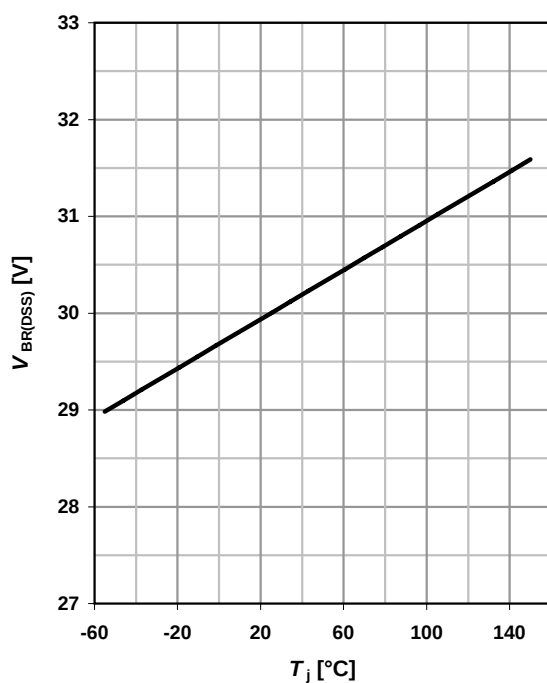
$$V_{GS}=f(Q_{\text{gate}}); I_D=-2\ \text{A pulsed}$$

parameter:  $V_{DD}$



### 15 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=250\ \mu\text{A}$$

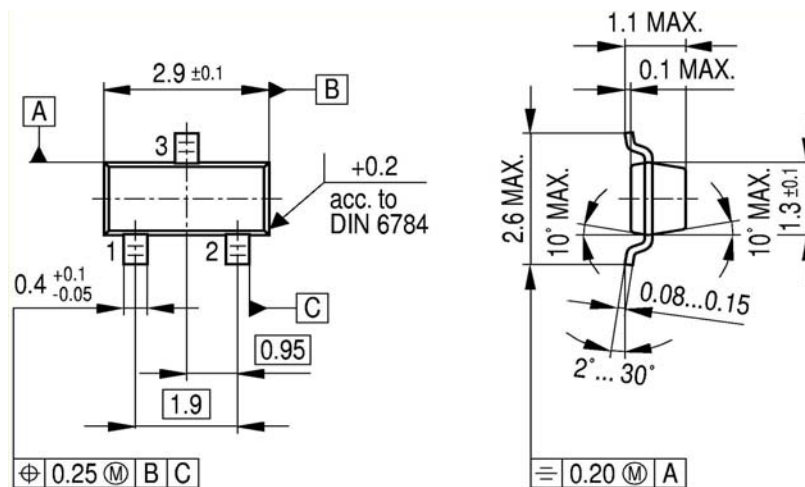


### 16 Gate charge waveforms

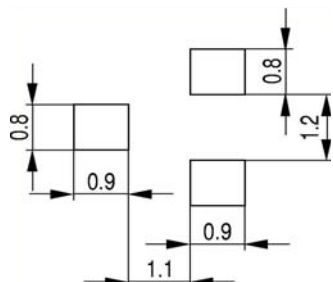


# SOT-23

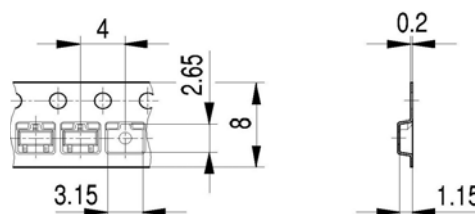
## Package Outline:



## Footprint:



## Packaging:



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